In the Abstract:

ABSTRACT OF THE DISCLOSURE

Thin film LED comprising a current expansion structure

In a A thin-film LED comprising an active layer (7) made of a nitride compound

semiconductor, which emits electromagnetic radiation (19) in a main radiation direction (15)[[,

a]]. A current expansion layer (9)[[, which]] is disposed downstream of the active layer (7) in the

main radiation direction (15) and is made of a first nitride compound semiconductor material, , a

main area (14), through which the The radiation emitted in the main radiation direction (15) is

coupled out through a main area (14), and a first contact layer (11, 12, 13) is arranged on the

main area (14), , the The transverse conductivity of the current expansion layer (9) is increased

by formation of a two-dimensional electron gas or hole gas. The two-dimensional electron gas or

hole gas is advantageously formed by embedding at least one layer (10) made of a second nitride

compound semiconductor material in the current expansion layer (9).

Significant Figure: Figure 1A

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